TOSHIBA Transistor Silicon NPN Triple Diffused Type (Darlington)

2SD1410A

High Voltage Switching Applications

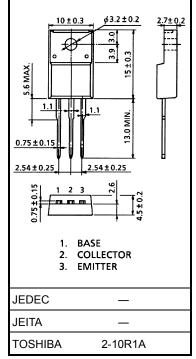
Industrial Applications

Unit: mm

• High DC current gain: $h_{FE} = 2000$ (min.) (VCE = 2 V, IC = 2 A)

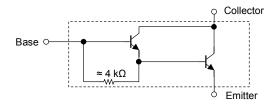
Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V _{CBO}	300	V	
Collector-emitter voltage		V _{CEO}	250	V	
Emitter-base voltage		V _{EBO}	5	V	
Collector current		Ιc	6	А	
Base current		Ι _Β	1	A	
Collector power dissipation	Ta = 25°C	Pc	2.0	w	
	Tc = 25°C		25		
Junction temperature		Тј	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	



Weight: 1.7 g (typ.)

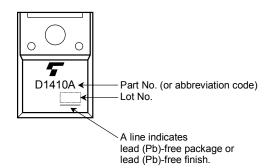
Equivalent Circuit



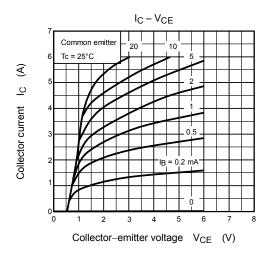
Electrical Characteristics (Ta = 25°C)

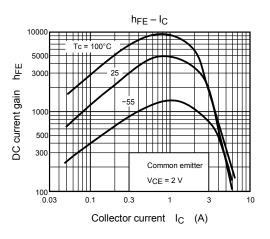
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off c	urrent	I _{CBO}	V _{CB} = 300 V, I _E = 0	_	_	0.5	mA
Emitter cut-off current		I _{EBO}	V _{EB} = 5 V, I _C = 0	_	_	0.5	mA
Collector-emitter breakdown voltage		V (BR) CEO	I _C = 10 mA, I _B = 0	250	_	_	V
DC current gain		h _{FE (1)}	V _{CE} = 2 V, I _C = 2 A	2000	_	_	
		h _{FE (2)}	V _{CE} = 2 V, I _C = 4 A	200	_	_	
Collector-emitter saturation voltage		V _{CE (sat)}	I _C = 4 A, I _B = 0.04 A	_	_	2.0	V
Base-emitter saturation voltage		V _{BE (sat)}	I _C = 4 A, I _B = 0.04 A	_	_	2.5	V
Collector output capacitance		C _{ob}	V _{CB} = 50 V, I _E = 0, f = 1 MHz	_	30	_	pF
Switching time S	Turn-on time	t _{on}	$20 \ \mu s$ $lnput$ $Input$ $Input$ $IB1$ $IB2$ $V_{CC} = 100 \ V$ $I_{B1} = -I_{B2} = 0.04 \ A, \ duty \ cycle \le 1\%$	_	1	_	
	Storage time	t _{stg}		_	8	_	μs
	Fall time	t _f		_	5	_	

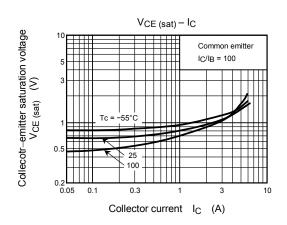
Marking

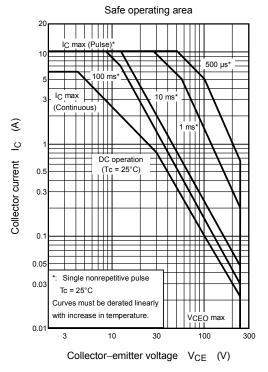


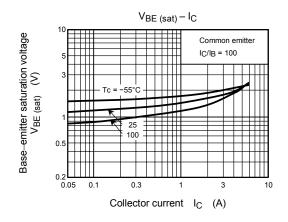
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